Ordering number : EN1895B

Silicon Epitaxial Planar Type (Cathode Common)

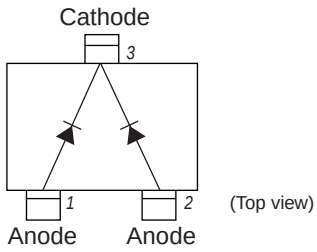
DCB010

Very High-Speed Switching Diode

Features

- Ideally suited for use in hybrid ICs because of very small-sized package.
- Fast switching speed.
- Small interterminal capacitance.

Electrical Connection

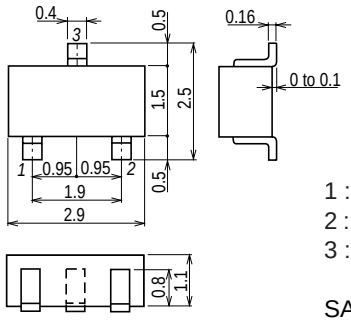


Package Dimensions

unit : mm

1169A

[DCB010]



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Peak Reverse Voltage	V_{RM}		85	V
Reverse Voltage	V_R		80	V
Peak Forward Current	I_{FM}		300	mA
	I_{FM}❋		450	mA
Average Rectified Current	I_O		100	mA
	I_O❋		150	mA
Surge Current (1μs)	I_{FSM}		4	A
	I_{FSM}❋		6	A
Allowable Power Dissipation	P		200	mW
Junction Temperature	Tj		125	°C
Storage Temperature	Tstg		−55 to +125	°C

❋ : Total value

SANYO Electric Co.,Ltd. Semiconductor Company

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward Voltage	V_{F1}	I_F=1mA		0.60		V
	V_{F2}	I_F=10mA		0.72		V
	V_{F3}	I_F=100mA			1.20	V
Reverse Current	I_{R1}	V_R=30V			0.1	μA
	I_{R2}	V_R=80V			0.5	μA
Interterminal Capacitance	C	V_R=0, f=1MHz			3.0	pF
Reverse Recovery Time	t_{rr}	I_F=10mA, V_R=6V, R_L=50Ω, I_{rr}=0.1Irp			4.0	ns

Marking : W6

Reverse Recovery Time Test Circuit